

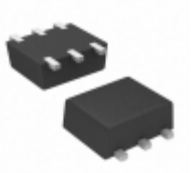
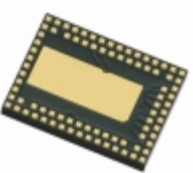


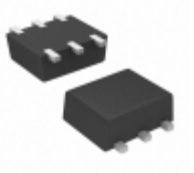

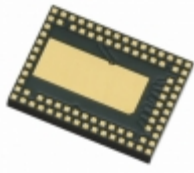
	<h2>SI1029X-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI1029X-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N/P-CH 60V SC89-6</p> <p>Datenblätter:  SI1029X-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 63000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI1029X-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N/P-CH 60V SC89-6
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	63000 pcs Stock
Hersteller Standard Vorlaufzeit	33 Weeks
detaillierte Beschreibung	Mosfet Array N and P-Channel 60V 305mA, 190mA
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	250mW
Verpackung / Gehäuse	SOT-563, SOT-666
Supplier Device-Gehäuse	SC-89-6
Typ FET	N and P-Channel
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	60V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	305mA, 190mA
Rds On (Max) @ Id, Vgs	1.4 Ohm @ 500mA, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	0.75nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	30pF @ 25V
Verpackung	Cut Tape (CT)
Basisteilenummer	SI1029
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI1029X-T1-GE3CT



















































SI1029X-T1-GE3 ist neu im Original, Suche SI1029X-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1029X-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI1029X-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI1030-A-GMR Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>	 <p>SI1029X-T1-GE3 Vishay / Siliconix MOSFET N/P-CH 60V SC89-6</p>	 <p>SI1027-B-GMR Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>	 <p>SI1029X-T1-E3 Electro-Films (EFI) / Vishay MOSFET N/P-CH 60V SOT563F</p>
 <p>SI1028X-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 30V SC89-6</p>	 <p>SI1029X-T1-E3 Vishay / Siliconix MOSFET N/P-CH 60V SOT563F</p>	 <p>SI1028X-T1-GE3 Vishay / Siliconix MOSFET 2N-CH 30V SC89-6</p>	 <p>SI1030-B-GM3R Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA</p>

heiße Teile

Mehr

Contact us: Info@Y-IC.com

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